



DOCUMENT CHANGE REQUEST

DCR number 1278 Changes required for: General

Date: 2019/09/06

Date sent: 2019/06/12

Status: IMPLEMENTED

Originator: Steve Thacker

Organisation: ESCC Executive Secretariat

Title: TRANSISTORS, POWER, MOSFET, N-CHANNEL,

Number: 5205/030

Issue: 1

Other documents affected:

Page:

7

Paragraph:

1.5 Note 1

Original wording:

As per 5205/030 issue 1

Proposed wording:

Safe Operating area figure for Variant 03 is amended; see attached mark-up specification 5205/030 Draft 2A for details.

Note: several additional minor editorial changes are included including the addition of ESCC reference spec hyperlinks and internal paragraph cross-references.

Justification:

This DCR is raised at the request of supporting ESCCQPL Manufacturer Infineon who have stated the following in justification:

1. We noticed that the RDSon limit-line has been calculated with the RDSon value at room temperature, instead of the one at $T_j(\text{max})$. We would like to correct this.
2. The DC and 10ms curves are slightly overrated, therefore the SOA screening test conditions are too tight. We would like to relax the test conditions and decrease the SOA.

Attachments:

esc5205030iss2_done.docx

Modifications:

N/A

Approval signature:

A handwritten signature in black ink, appearing to read "Stephen R. ...".

Date signed:

2019-09-06